

# Power MOSFET 20V, 160m $\Omega$ , 2A, Dual N-Channel

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#### **Features**

- ON-Resistance Nch :  $RDS(on)1=120m\Omega$  (typ)
- · 1.8V Drive
- · ESD Diode Protected Gate
- · Pb-Free, Halogen Free and RoHS Compliance

#### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Value	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		2.0	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	8.0	Α
Power Dissipation	PD	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm) 1unit	0.8	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **Thermal Resistance Ratings**

Parameter	Symbol	Value	Unit	
Junction to Ambient	$R_{\theta JA}$	156.25	°C/W	
When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm) 1unit			C/ VV	

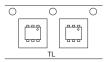
#### **Product & Package Information**

• Package : MCPH6

• JEITA, JEDEC : SC-88, SC-70-6, SOT-363

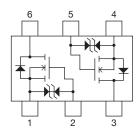
• Minimum Packing Quantity : 3,000 pcs./reel

#### Packing Type: TL Marking





#### **Electrical Connection**



#### ORDERING INFORMATION

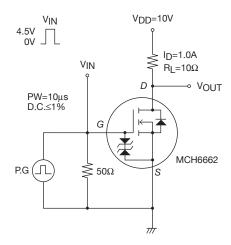
See detailed ordering and shipping information on page 6 of this data sheet.

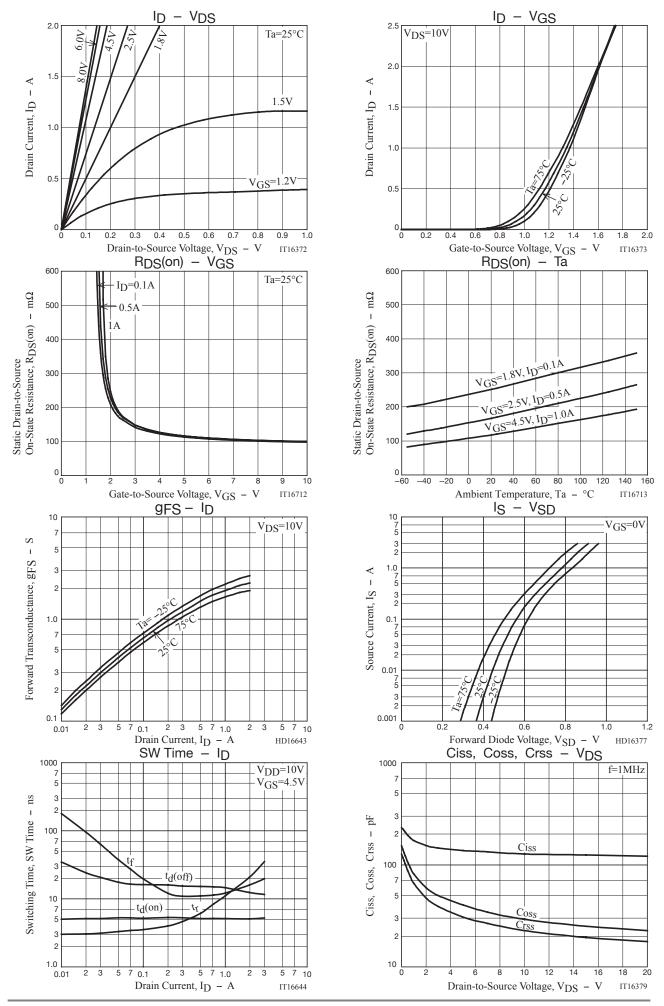
#### **Electrical Characteristics** at Ta=25°C

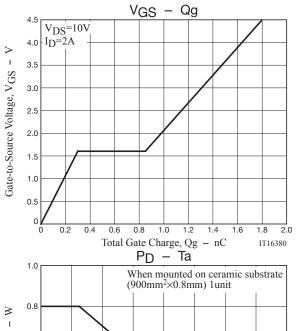
Parameter	Cumple of	Conditions	Value			Unit
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ
Gate Threshold Voltage	V <sub>GS</sub> (th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transconductance	9FS	V <sub>DS</sub> =10V, I <sub>D</sub> =1A		1.9		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=1.0A, VGS=4.5V		120	160	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =0.5A, V <sub>GS</sub> =2.5V		170	240	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =0.1A, V <sub>GS</sub> =1.8V		255	380	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		128		pF
Output Capacitance	Coss			28		pF
Reverse Transfer Capacitance	Crss			21		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		5.1		ns
Rise Time	t <sub>r</sub>			11		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)			14.5		ns
Fall Time	t <sub>f</sub>			12		ns
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A		1.8		nC
Gate-to-Source Charge	Qgs			0.3		nC
Gate-to-Drain "Miller" Charge	Qgd			0.55		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =2A, V <sub>GS</sub> =0V		0.85	1.2	V

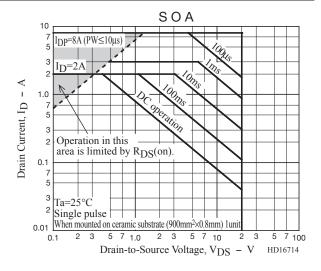
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

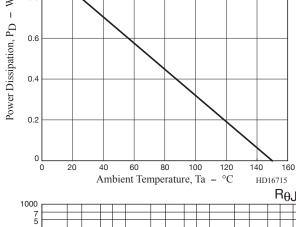
#### **Switching Time Test Circuit**

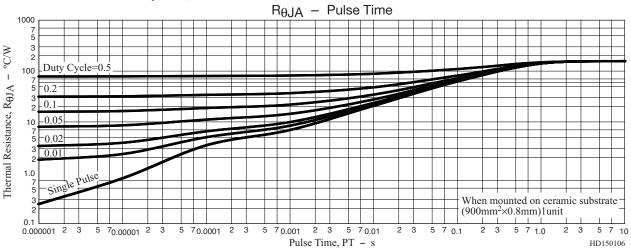










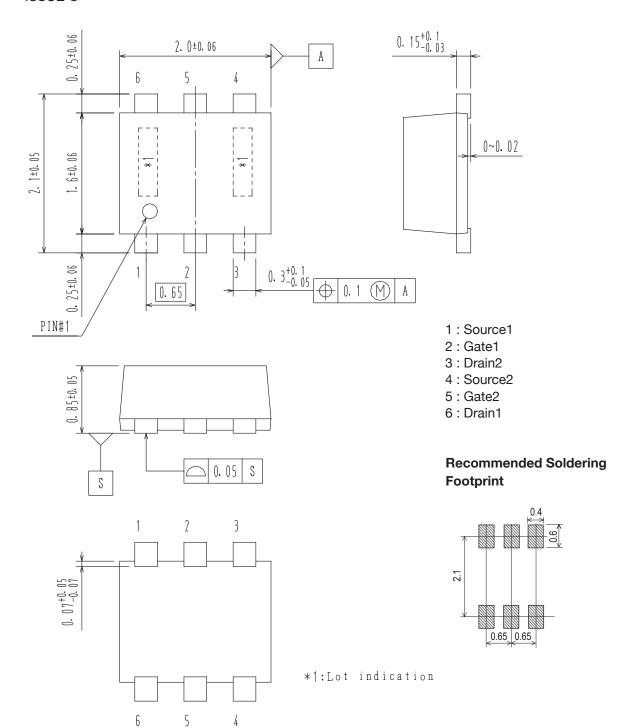


#### **Package Dimensions**

unit : mm

MCH6662-TL-H, MCH6662-TL-W

## SC-88FL / MCPH6 CASE 419AS ISSUE O



#### **ORDERING INFORMATION**

Device	Package	Shipping	memo	
MCH6662-TL-H	MCPH6	2.000pag /raal	Pb-Free and Halogen Free	
MCH6662-TL-W	IVICPHO	3,000pcs./reel		

Note on usage: Since the MCH6662 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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